

# Far UV Sensor

## GFUV-T10GD-L



**Features**

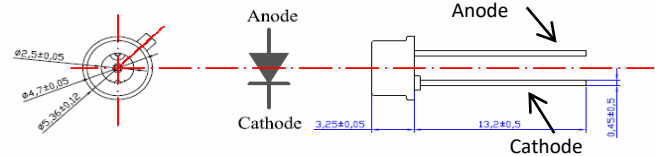
- Aluminium Gallium Nitride Based Material
- Schottky-type Photodiode
- Photovoltaic Mode Operation
- Good Solar Blindness



**Applications**

- Far UV Monitoring
- Excimer Lamp Monitoring

### Outline Diagrams and Dimensions



### Absolute Maximum Ratings

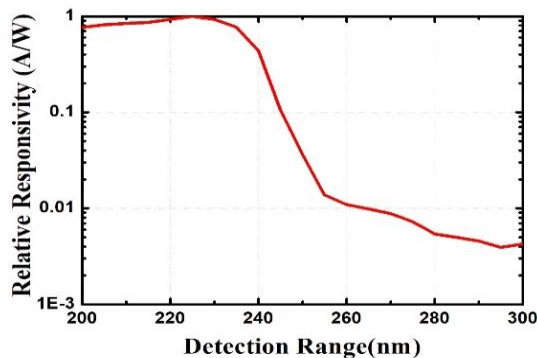
Parameter	Symbol	Min.	Max.	Unit	Remark
Storage Temperature	$T_{st}$	-40	90	°C	
Operating Temperature	$T_{op}$	-30	85	°C	
Reverse Voltage	$V_{r, max.}$		2	V	
Forward Current	$I_{f, max.}$		1	mA	
Optical Source Power Range	$P_{opt}$	0.1m	100m	W/cm <sup>2</sup>	Excimer Lamp
Soldering Temperature	$T_{sol}$		260	°C	within 10 sec.

※Notice: apply to us in the case that Optical Source Power is over 100mW/cm<sup>2</sup>.

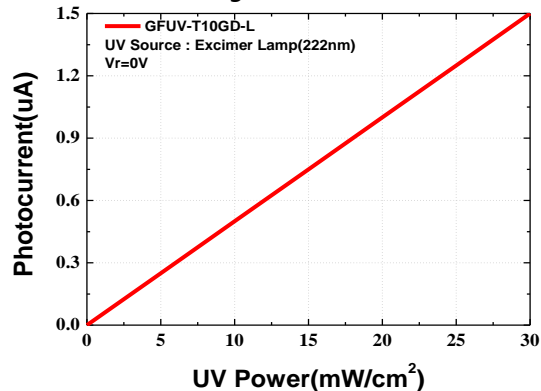
### Characteristics (at 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Dark Current	$I_d$			100	pA	$V_r = 1\text{ V}$
Photo Current	$I_{ph}$	45	50	55	nA	222nm peak FUV Lamp, 1mW/cm <sup>2</sup>
		2.12	2.35	2.58	nA	172nm peak VUV Lamp, 1mW/cm <sup>2</sup>
Spectral Detection range	$\lambda$			245	nm	
Active area			1.536		mm <sup>2</sup>	

### Relative Responsivity(A/W)



### Photocurrent along UV Power



### Caution

ESD can damage the device hence please avoid ESD. Insulate the cap of TO-CAN or it can cause malfunction of the device.